AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A solid-state image sensing apparatus that performs for performing photoelectric conversion of incident light, the solid-state image sensing apparatus comprising:

a photosensitive unit in which a plurality of photoelectric conversion circuits is are

arranged laid out one-dimensionally or two-dimensionally, each of said the photoelectric

conversion circuits corresponding to one of a plurality of pixel pixels, and each of the

photoelectric conversion circuits including a photodiode that accumulates for accumulating

electric charge by performing the photoelectric conversion of incident light and an output circuit

that outputs for outputting the accumulated electric charge as an electric signal;

an electric charge simultaneous removal unit operable to simultaneously remove the accumulated electric charge in <u>each of</u> the photodiodes <u>laid-out disposed</u> in a predetermined region to be read out in the photosensitive unit; and

an electric charge accumulation unit operable to accumulate electric charge in <u>each of</u> the <u>photodiode photodiodes laid out disposed</u> in the region to be read out during a predetermined time after the accumulated electric charge in <u>each of</u> the <u>photodiode photodiodes</u> that is laid out <u>disposed</u> in the region to be read out is removed,

wherein the output circuit in each of the photoelectric conversion circuits includes:

a first transistor for receiving a readout signal from the electric charge
simultaneous removal unit and which allows the electric charge accumulated in the photodiode to
pass therethrough in response to activation of the readout signal; and

an electric charge retention unit operable to receive the electric charge that passes through the first transistor and to retain the electric charge;

a second transistor which allows the electric signal to pass therethrough, the electric signal being based on a value of voltage determined by the electric charge retained by the electric charge retention unit; and

a reset circuit for receiving a reset signal from the electric charge simultaneous removal unit and for resetting an amount of electric charge accumulated in the electric charge retention unit in response to activation of the reset signal, and

wherein the electric charge simultaneous removal unit simultaneously outputs the readout signal and the reset signal to all of the photoelectric conversion circuits disposed in the region to be read out.

2. (Currently Amended) The solid-state image sensing apparatus according to Claim 1,

wherein the electric charge accumulation unit generates an electric accumulation start signal to start electric charge accumulation to for each of the photodiode laid out photodiodes disposed in the region to be read out.

3. (Currently Amended) The solid-state image sensing apparatus according to Claim 2, wherein the electric charge accumulation unit generates an electric accumulation end signal and ends electric charge accumulation to for each of the photodiode laid out photodiodes

<u>disposed</u> in the region to be read out in response to activation of the electric charge accumulation end signal.

4. (Currently Amended) The solid-state image sensing apparatus according to Claim 2, further comprising an incident light control unit operable to control incidence of light into the photosensitive unit,

wherein the electric charge accumulation unit ends electric charge accumulation to <u>each</u>
of the <u>photodiode laid out photodiodes disposed</u> in the region to be read out using the incident light control unit by blocking out incidence of light into the photosensitive unit.

5. (Currently Amended) The solid-state image sensing apparatus according to Claim 1, further comprising an incident light control unit operable to control incidence of light into the photosensitive unit,

wherein the electric charge accumulation unit starts incidence of light to the photosensitive unit using the incident light control unit after the electric charge simultaneous removal unit simultaneously removes the accumulated electric charge to for each of the photodiode laid out photodiodes disposed in the region to be read out.

6. (Currently Amended) The solid-state image sensing apparatus according to Claim 5, wherein the electric charge accumulation unit generates an electric accumulation end signal and ends electric charge accumulation to for each of the photodiode laid out photodiodes

<u>disposed</u> in the region to be read out in response to activation of the electric charge accumulation end signal.

- 7. (Currently Amended) The solid-state image sensing apparatus according to Claim 5, wherein the electric charge accumulation unit ends electric charge accumulation to for each of the photodiode laid out photodiodes disposed in the region to be read out using the incident light control unit by blocking out incidence of light into the photosensitive unit.
 - **8.** (Currently Amended) The solid-state image sensing apparatus according to Claim 5, wherein the incident light control unit includes:
- a liquid crystal shutter that is set up <u>disposed</u> between the photosensitive unit and an object to be photographed; and
- a liquid crystal shutter control unit operable to apply a predetermined voltage to the liquid crystal shutter to control <u>a penetration of light</u>.
- 9. (Currently Amended) The solid-state image sensing apparatus according to Claim 1, wherein the electric charge simultaneous removal unit simultaneously outputs [[a]] the reset signal to all of the photoelectric conversion circuits laid out disposed in the region to be read out; and

the output circuit in the photoelectric conversion circuit includes:

a first transistor that receives the reset signal from the electric charge simultaneous

removal unit and that resets electric charge accumulated in the photodiode in response to activation of said reset signal; and

a second transistor that lets the electric signal pass through, the electric signal according to value of voltage determined by electric charge outputted from the photodiode.

- 10. (Currently Amended) The solid-state image sensing apparatus according to Claim 9, wherein the electric charge simultaneous removal unit generates a gate signal and includes a reset signal passage switch that <u>simultaneously</u> outputs <u>simultaneously</u> the reset signal to all <u>of</u> the photoelectric conversion circuits in response to activation of the gate signal.
- 11. (Currently Amended) The solid-state image sensing apparatus according to Claim 9, wherein the electric charge simultaneous removal unit includes:
 - a switch transistor that serves as a switch; and
- a capacitor that is set up disposed between a gate and a source or a drain of the switch transistor, and

wherein, when the capacitor is charged, the reset signal is inputted from the drain of the switch transistor and is outputted simultaneously to all of the photoelectric conversion circuits from the source.

12. (Canceled)

13. (Currently Amended) A solid-state image sensing apparatus for performing photoelectric conversion of incident light, the solid-state image sensing apparatus comprising:

a photosensitive unit in which a plurality of photoelectric conversion circuits are arranged one-dimensionally or two-dimensionally, each of the photoelectric conversion circuits corresponding to one of a plurality of pixels, and each of the photoelectric conversion circuits including a photodiode for accumulating electric charge by performing the photoelectric conversion of incident light and an output circuit for outputting the accumulated electric charge as an electric signal;

an electric charge simultaneous removal unit operable to simultaneously remove the accumulated electric charge in each of the photodiodes disposed in a predetermined region to be read out in the photosensitive unit; and

an electric charge accumulation unit operable to accumulate electric charge in each of the photodiodes disposed in the region to be read out during a predetermined time after the accumulated electric charge in each of the photodiodes disposed in the region to be read out is removed,

wherein the electric charge simultaneous removal unit simultaneously outputs a readout signal and a reset signal to all of the photoelectric conversion circuits disposed in the region to be read out.

wherein the output circuit in each of the photoelectric conversion circuits includes:

a first transistor for receiving a readout signal from the electric charge

simultaneous removal unit and which allows the electric charge accumulated in the photodiode to

pass therethrough in response to activation of the readout signal; and

an electric charge retention unit operable to receive the electric charge that passes through the first transistor and to retain the electric charge;

a second transistor which allows the electric signal to pass therethrough, the
electric signal being based on a value of voltage determined by the electric charge retained by the
electric charge retention unit; and

a reset circuit for receiving a reset signal from the electric charge simultaneous removal unit and for resetting an amount of electric charge accumulated in the electric charge retention unit in response to activation of the reset signal.

The wherein the solid-state image sensing apparatus according to Claim 12, further comprising comprises an electric signal readout unit operable to read out the electric signal signals outputted from the photoelectric conversion circuit laid out circuits disposed in the region to be read out,

wherein the electric signal readout unit includes:

a first unit operable to output the activated reset signal to the <u>each of the</u> reset <u>eircuit circuits</u> in the photoelectric conversion <u>eircuit laid out circuits disposed</u> in the region to be read out; and

a second unit operable to output the activated readout signal to said each of the reset eireuit circuits disposed in the region to be read out after outputting said the reset signal, and

wherein the first unit outputs the activated reset signal activated after the predetermined

time in the electric charge accumulation unit has passed.

14. (Currently Amended) The solid-state image sensing apparatus according to Claim13,

wherein the electric signal readout unit <u>simultaneously</u> reads out <u>simultaneously</u> the accumulated electric charge of <u>each of</u> the <u>photodiode laid out photodiodes disposed</u> in the region to be read out.

15. (Currently Amended) The solid-state image sensing apparatus according to Claim 13, further comprising a frame memory that can <u>simultaneously</u> store <u>simultaneously</u> all <u>of</u> the electric signals outputted from the photoelectric conversion <u>eireuit laid out circuits disposed</u> in the region to be read out,

wherein the electric signal readout unit <u>simultaneously</u> transmits simultaneously to the frame memory the electric signals outputted from the photoelectric conversion circuit laid out <u>circuits disposed</u> in the region to be read out.

16. (Currently Amended) The solid-state image sensing apparatus according to Claim 13, further comprising the a frame memory that can simultaneously store simultaneously all of the electric signals outputted from the photoelectric conversion eireuit laid out circuits disposed in the region to be read out,

wherein the electric signal readout unit writes to the frame memory in sequence the

electric signals outputted from the photoelectric conversion eircuit laid out circuits disposed in the region to be read out within a short period of time which ean be is negligible compared with the predetermined time in the electric charge accumulation unit.

17. (Currently Amended) A solid-state image sensing apparatus for performing photoelectric conversion of incident light, the solid-state image sensing apparatus comprising:

a photosensitive unit in which a plurality of photoelectric conversion circuits are arranged one-dimensionally or two-dimensionally, each of the photoelectric conversion circuits corresponding to one of a plurality of pixels, and each of the photoelectric conversion circuits including a photodiode for accumulating electric charge by performing the photoelectric conversion of incident light and an output circuit for outputting the accumulated electric charge as an electric signal;

an electric charge simultaneous removal unit operable to simultaneously remove the accumulated electric charge in each of the photodiodes disposed in a predetermined region to be read out in the photosensitive unit; and

an electric charge accumulation unit operable to accumulate electric charge in each of the photodiodes disposed in the region to be read out during a predetermined time after the accumulated electric charge in each of the photodiodes disposed in the region to be read out is removed,

wherein the electric charge simultaneous removal unit simultaneously outputs a readout signal and a reset signal to all of the photoelectric conversion circuits disposed in the region to be

read out,

wherein the output circuit in each of the photoelectric conversion circuits includes:

a first transistor for receiving a readout signal from the electric charge
simultaneous removal unit and which allows the electric charge accumulated in the photodiode to
pass therethrough in response to activation of the readout signal; and

an electric charge retention unit operable to receive the electric charge that passes
through the first transistor and to retain the electric charge;

a second transistor which allows the electric signal to pass therethrough, the electric signal being based on a value of voltage determined by the electric charge retained by the electric charge retention unit; and

a reset circuit for receiving a reset signal from the electric charge simultaneous removal unit and for resetting an amount of electric charge accumulated in the electric charge retention unit in response to activation of the reset signal.

wherein The the solid-state image sensing apparatus according to Claim 12, further emprising comprises an electric signal readout unit operable to read out the electric signal signals outputted from the photoelectric conversion eircuit laid out circuits disposed in the region to be read out,

wherein the electric signal readout unit includes:

a first unit operable to output the activated reset signal to <u>each of</u> the reset <u>eireuit</u> <u>circuits</u> in the photoelectric conversion <u>eireuit laid out circuits disposed</u> in the region to be read out; and

a second unit operable to output the activated readout signal to said each of the reset eircuit circuits disposed in the region to be read out after outputting said the reset signal, and

wherein the first unit outputs the <u>activated</u> reset signal activated before the predetermined time in the electric charge accumulation unit has passed.

18. (Currently Amended) The solid-state image sensing apparatus according to Claim17,

wherein the first unit outputs the activated reset signal at a time which overlaps in overlapping time of a period before the predetermined time in the electric charge accumulation unit has passed and a period during which the electric charge simultaneous removal unit outputs the activated reset signal.

19. (Currently Amended) A solid-state image sensing apparatus for performing photoelectric conversion of incident light, the solid-state image sensing apparatus comprising:

a photosensitive unit in which a plurality of photoelectric conversion circuits are arranged one-dimensionally or two-dimensionally, each of the photoelectric conversion circuits corresponding to one of a plurality of pixels, and each of the photoelectric conversion circuits including a photodiode for accumulating electric charge by performing the photoelectric conversion of incident light and an output circuit for outputting the accumulated electric charge as an electric signal;

an electric charge simultaneous removal unit operable to simultaneously remove the accumulated electric charge in each of the photodiodes disposed in a predetermined region to be read out in the photosensitive unit; and

an electric charge accumulation unit operable to accumulate electric charge in each of the photodiodes disposed in the region to be read out during a predetermined time after the accumulated electric charge in each of the photodiodes disposed in the region to be read out is removed,

wherein the electric charge simultaneous removal unit simultaneously outputs a readout signal and a reset signal to all of the photoelectric conversion circuits disposed in the region to be read out,

wherein the output circuit in each of the photoelectric conversion circuits includes:

a first transistor for receiving a readout signal from the electric charge
simultaneous removal unit and which allows the electric charge accumulated in the photodiode to
pass therethrough in response to activation of the readout signal; and

an electric charge retention unit operable to receive the electric charge that passes through the first transistor and to retain the electric charge;

a second transistor which allows the electric signal to pass therethrough, the
electric signal being based on a value of voltage determined by the electric charge retained by the
electric charge retention unit; and

a reset circuit for receiving a reset signal from the electric charge simultaneous removal unit and for resetting an amount of electric charge accumulated in the electric charge

retention unit in response to activation of the reset signal,

wherein the The solid-state image sensing apparatus according to Claim 12, further comprising comprises an electric signal readout unit operable to read out the electric signal signals outputted from the photoelectric conversion circuit laid out circuits disposed in the region to be read out,

wherein the electric signal readout unit includes:

a first unit operable to output the activated reset signal to <u>each of</u> the reset <u>eireuit</u> <u>circuits</u> in the photoelectric conversion <u>eireuit laid out</u> <u>circuits disposed</u> in the region to be read out; and

a second unit operable to output the activated readout signal to said each of the reset eireuit circuits after outputting said the reset signal, and

wherein the first unit outputs the activated reset signal for a period since some starting from a mid point of the predetermined time until an end of said the predetermined time in the electric charge accumulation unit.

20. (Currently Amended) The solid-state image sensing apparatus according to Claim 12 1,

wherein the electric charge simultaneous removal unit generates a gate signal and includes a readout signal passage switch that outputs for simultaneously outputting the readout signal to all of the photoelectric conversion circuits in response to the gate signal.

21. (Currently Amended) The solid-state image sensing apparatus according to Claim12 1,

wherein the electric charge simultaneous removal unit includes:

a switch transistor that serves as a switch; and

a capacitor that is set up <u>disposed</u> between a gate and a source or a drain of the switch transistor, and

wherein, when the capacitor is charged, the reset signal is inputted from the drain of the switch transistor and is outputted simultaneously to all of the photoelectric conversion circuits from the source.

22. (Currently Amended) A camera that photographs for photographing an object, the camera comprising:

a solid-state image sensing apparatus; and

a mechanical shutter,

wherein the solid-state image sensing apparatus includes:

a photosensitive unit in which a plurality of photoelectric conversion circuits is are

arranged laid out one-dimensionally or two-dimensionally, each of said the photoelectric

conversion circuits corresponding to one of a plurality of pixel pixels, and each of the

photoelectric conversion circuits including a photodiode that accumulates for accumulating

electric charge by performing the photoelectric conversion of incident light and an output circuit

that outputs for outputting the accumulated electric charge as an electric signal;

an electric charge simultaneous removal unit operable to simultaneously remove the accumulated electric charge in <u>each of</u> the photodiodes <u>laid out disposed</u> in a predetermined region to be read out in the photosensitive unit; and

an electric charge accumulation unit operable to accumulate electric charge in <u>each of</u> the <u>photodiode photodiodes laid out disposed</u> in the region to be read out during a predetermined time after the accumulated electric charge in <u>each of</u> the <u>photodiode photodiodes</u> that is laid out disposed in the region to be read out is removed; and

an incident light control unit operable to control incidence of light into the photosensitive unit,

wherein the mechanical shutter is set up <u>disposed</u> between the photosensitive unit of the solid-state image sensing apparatus and an object to be photographed,

wherein the electric charge accumulation unit ends electric charge accumulation to the photodiode laid out photodiodes disposed in the region to be read out using the incident light control unit by blocking out incidence of light into the photosensitive unit, and

wherein the incident light control unit controls incidence of light into the photosensitive unit by controlling opening and shutting of the mechanical shutter.

wherein the output circuit in each of the photoelectric conversion circuits includes:

a first transistor for receiving a readout signal from the electric charge
simultaneous removal unit and which allows the electric charge accumulated in the photodiode to
pass therethrough in response to activation of the readout signal; and

an electric charge retention unit operable to receive the electric charge that passes

through the first transistor and to retain the electric charge;

a second transistor which allows the electric signal to pass therethrough, the electric signal being based on a value of voltage determined by the electric charge retained by the electric charge retention unit; and

a reset circuit for receiving a reset signal from the electric charge simultaneous removal unit and for resetting an amount of electric charge accumulated in the electric charge retention unit in response to activation of the reset signal, and

wherein the electric charge simultaneous removal unit simultaneously outputs the readout signal and the reset signal to all of the photoelectric conversion circuits disposed in the region to be read out.

23. (Currently Amended) An image sensing method for photographing an object using a solid-state sensing apparatus,

wherein the solid-state image sensing apparatus includes a photosensitive unit in which a plurality of photoelectric conversion circuits is laid out are arranged one-dimensionally or two-dimensionally, each of said the photoelectric conversion circuits corresponding to one of a plurality of pixel pixels, and each of the photoelectric conversion circuits including a photodiode that accumulates for accumulating electric charge by performing the photoelectric conversion of incident light and an output circuit that outputs for outputting the accumulated electric charge as an electric signal,

wherein the output circuit in each of the photoelectric conversion circuits includes:

a first transistor for receiving a readout signal from the electric charge
simultaneous removal unit and which allows the electric charge accumulated in the photodiode to
pass therethrough in response to activation of the readout signal; and

an electric charge retention unit operable to receive the electric charge that passes through the first transistor and to retain the electric charge;

a second transistor which allow the electric signal to pass therethrough, the electric signal being based on a value of voltage determined by the electric charge retained by the electric charge retention unit; and

a reset circuit for receiving a reset signal from the electric charge simultaneous removal unit and for resetting an amount of electric charge accumulated in the electric charge retention unit in response to activation of the reset signal, and

wherein the electric charge simultaneous removal unit simultaneously outputs the readout signal and the reset signal to all of the photoelectric conversion circuits disposed in the region to be read out, and

wherein the image sensing method comprising comprises the steps of:

simultaneously removing the accumulated electric charge in <u>each of</u> the <u>photodiode</u>

photodiodes by simultaneously outputting the readout signal and the reset signal to all of the

photoelectric conversion circuits <u>laid out disposed</u> in a predetermined region to be read out in the photosensitive unit; and

accumulating electric charge in <u>each of</u> the <u>photodiode laid out photodiodes disposed</u> in the region to be read out during a predetermined time after the accumulated electric charge of the

photodiode photodiodes that is laid out disposed in the region is removed.

24. (New) The solid-state image sensing apparatus according to Claim 1, wherein the electric charge simultaneous removal unit aligns a pulse of the reset signal and a pulse of the readout signal, and simultaneously outputs the readout signal and the reset signal to all of the photoelectric conversion circuits disposed in the region to be read out.

25. (New) The solid-state image sensing apparatus according to Claim 1,

wherein the electric charge simultaneous removal unit simultaneously outputs the readout signal and the reset signal to all of the photoelectric conversion circuits disposed in the region to be read out, the reset signal having a width of a pulse that is wider than a width of a pulse of the readout signal.